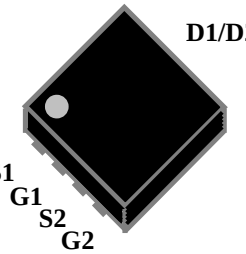
AP4500GYT-HF

Halogen-Free Product

Advanced Power Electronics Corp.

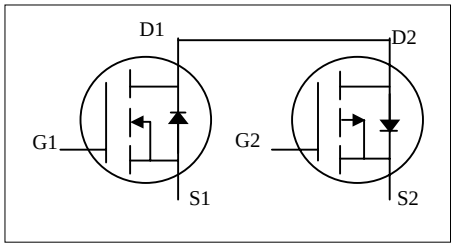
N AND P-CHANNEL ENHANCEMENT MODE POWER MOSFET

- ▼ Simple Drive Requirement
- ▼ Good Thermal Performance
- ▼ Fast Switching Performance
- ▼ RoHS Compliant & Halogen-Free



PMPAK® 3x3

N-CH	BV_{DSS}	20V
	$R_{DS(ON)}$	21mΩ
	I_D	8.9A
P-CH	BV_{DSS}	-20V
	$R_{DS(ON)}$	60mΩ
	I_D	-5.3A



Description

AP4500 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The PMPAK® 3x3 is special for voltage conversion application using standard infrared reflow technique with the backside heat sink to achieve the good thermal performance.

Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-channel	P-channel	
V_{DS}	Drain-Source Voltage	20	-20	V
V_{GS}	Gate-Source Voltage	±12	±12	V
I_D@T_A=25℃	Continuous Drain Current[3]	8.9	-5.3	A
I_D@T_A=70℃	Continuous Drain Current[3]	7.1	-4.3	A
I_{DM}	Pulsed Drain Current[1]	20	-20	A
P_D@T_A=25℃	Total Power Dissipation	2.5		W
T_{STG}	Storage Temperature Range	-55 to 150		℃
T_J	Operating Junction Temperature Range	-55 to 150		℃

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	10	℃/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient[3]	50	℃/W

N-CH Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	20	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=4.5V, I_D=8A	-	16.6	21	mΩ
		V_{GS}=2.5V, I_D=4A	-	25.4	36	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	0.5	0.75	1.5	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=4A	-	18	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=16V, V_{GS}=0V	-	-	10	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±12V, V_{DS}=0V	-	-	±100	nA
Q_g	Total Gate Charge	I_D=4A	-	8	12.8	nC
Q_{gs}	Gate-Source Charge	V_{DS}=16V	-	1.1	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=4.5V	-	4	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=10V	-	11	-	ns
t_r	Rise Time	I_D=1A	-	10	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω	-	16	-	ns
t_f	Fall Time	V_{GS}=5V	-	6	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	450	720	pF
C_{oss}	Output Capacitance	V_{DS}=10V	-	140	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	130	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=2.1A, V_{GS}=0V	-	-	1.2	V
t_{rr}	Reverse Recovery Time	I_S=6A, V_{GS}=0V	-	21	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	14	-	nC

P-CH Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250uA	-20	-	-	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-4.5V, I_D=-5A	-	45.8	60	mΩ
		V_{GS}=-2.5V, I_D=-3A	-	62.6	90	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250uA	-0.5	-0.73	-1.5	V
g_{fs}	Forward Transconductance	V_{DS}=-10V, I_D=-3A	-	12	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-16V, V_{GS}=0V	-	-	-10	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±12V, V_{DS}=0V	-	-	±100	nA
Q_g	Total Gate Charge	I_D=-3A	-	9	14.4	nC
Q_{gs}	Gate-Source Charge	V_{DS}=-16V	-	1.3	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=-4.5V	-	3	-	nC
$t_{d(on)}$	Turn-on Delay Time	V_{DS}=-10V	-	8	-	ns
t_r	Rise Time	I_D=-1A	-	15	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3.3Ω	-	26	-	ns
t_f	Fall Time	V_{GS}=-5V	-	21	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	710	1140	pF
C_{oss}	Output Capacitance	V_{DS}=-10V	-	125	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	110	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Forward On Voltage[2]	I_S=-2.1A, V_{GS}=0V	-	-	-1.2	V
t_{rr}	Reverse Recovery Time	I_S=-3A, V_{GS}=0V	-	19	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=-100A/μs	-	10	-	nC

Notes:

1.Pulse width limited by Max. junction temperature.

2.Pulse test

3.Surface mounted on 1 in^2 copper pad of FR4 board, t ≤10sec, 90°C/W at steady state.

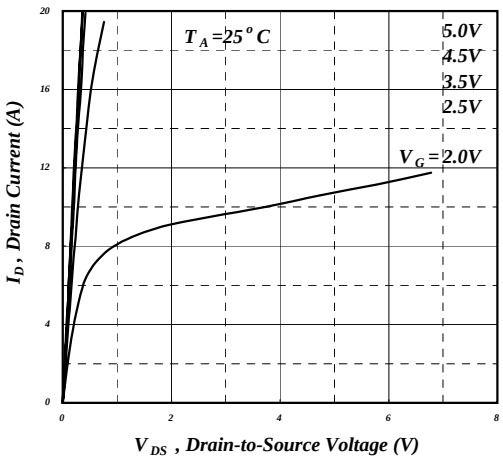


Fig 1. Typical Output Characteristics

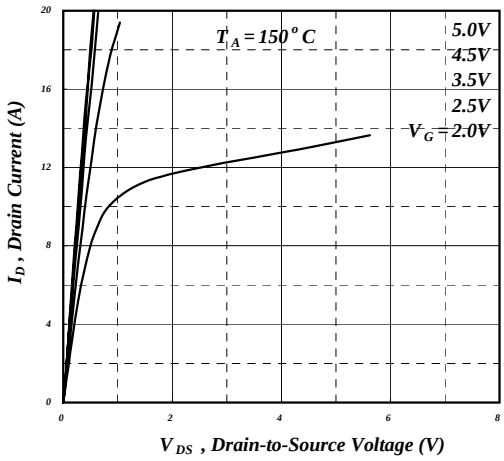


Fig 2. Typical Output Characteristics

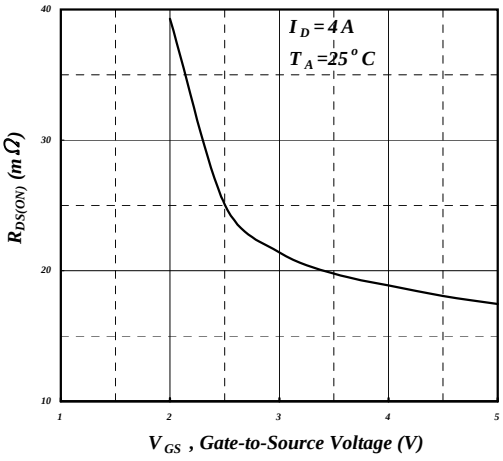


Fig 3. On-Resistance v.s. Gate Voltage

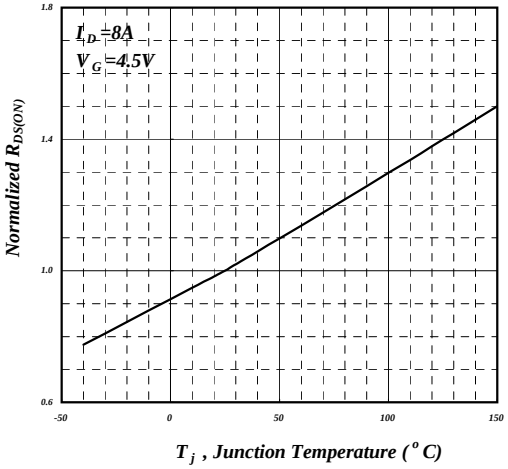


Fig 4. Normalized On-Resistance v.s. Junction Temperature

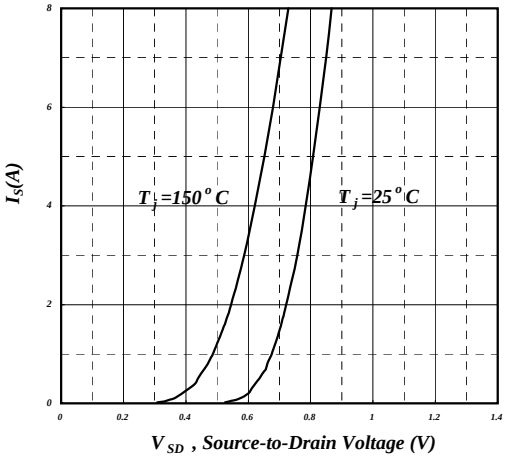


Fig 5. Forward Characteristic of Reverse Diode

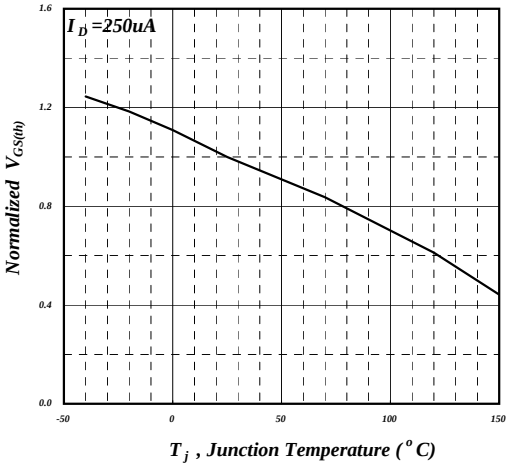


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

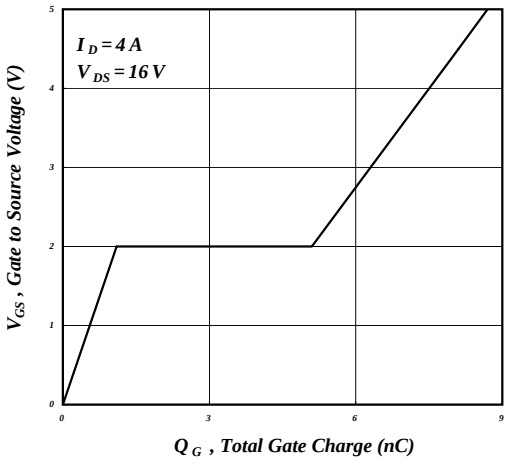


Fig 7. Gate Charge Characteristics

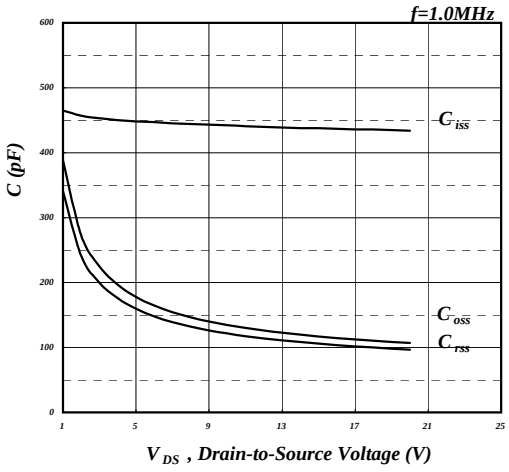


Fig 8. Typical Capacitance Characteristics

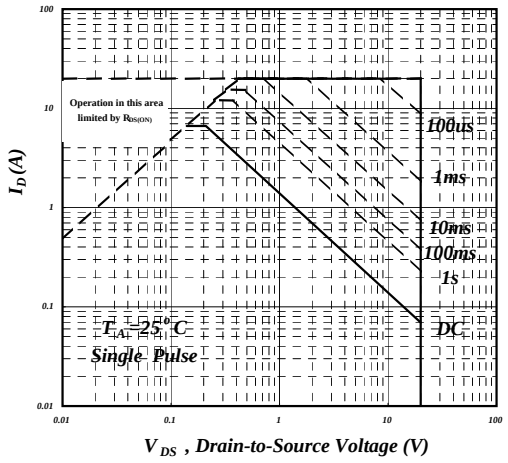


Fig 9. Maximum Safe Operating Area

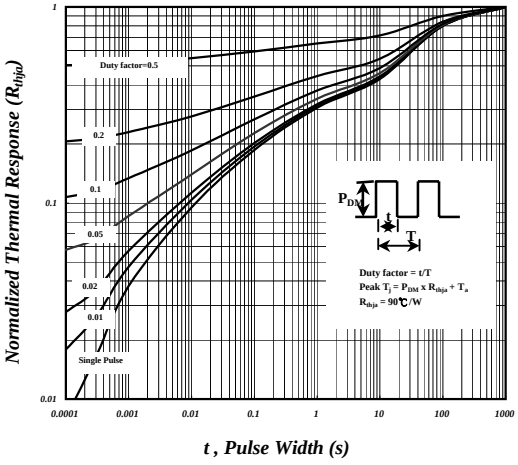


Fig 10. Effective Transient Thermal Impedance

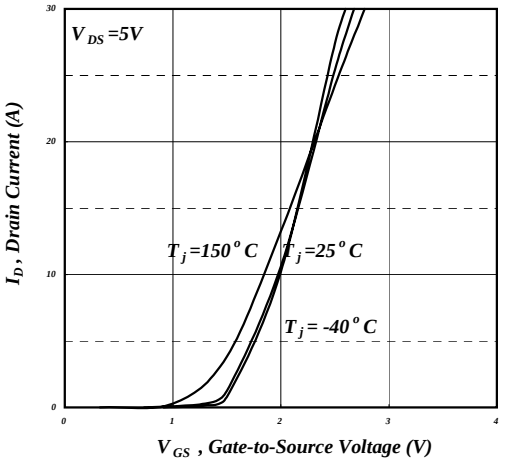


Fig 11. Transfer Characteristics

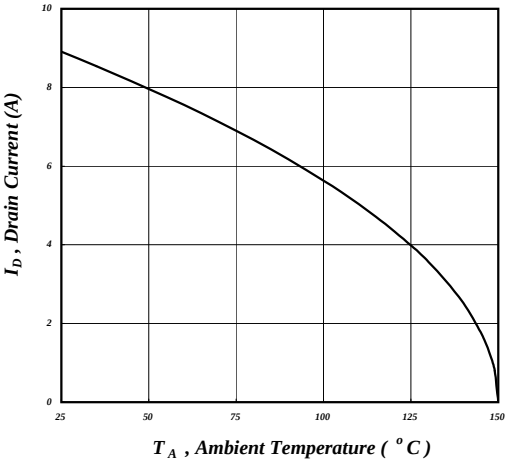


Fig 12. Maximum Continuous Drain Current v.s. Ambient Temperature

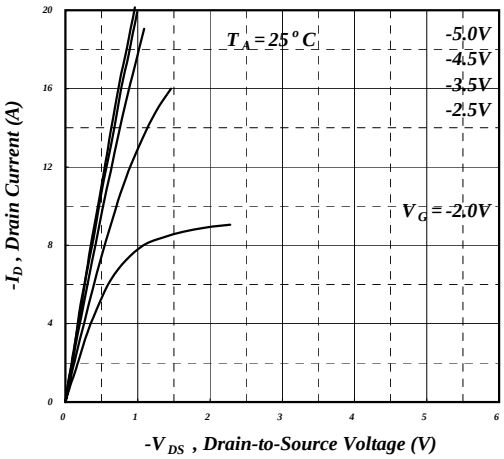


Fig 1. Typical Output Characteristics

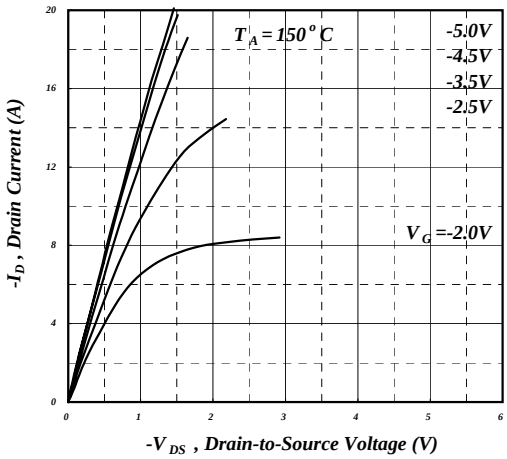


Fig 2. Typical Output Characteristics

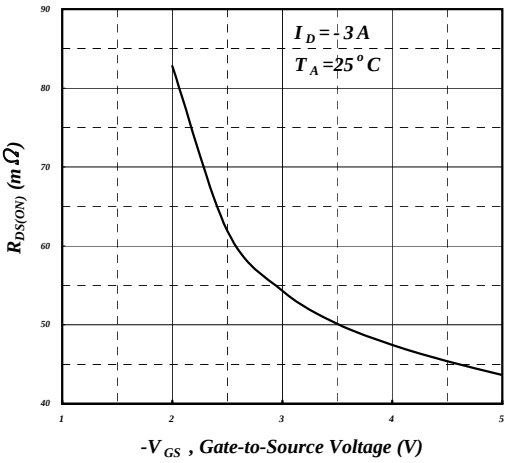


Fig 3. On-Resistance v.s. Gate Voltage

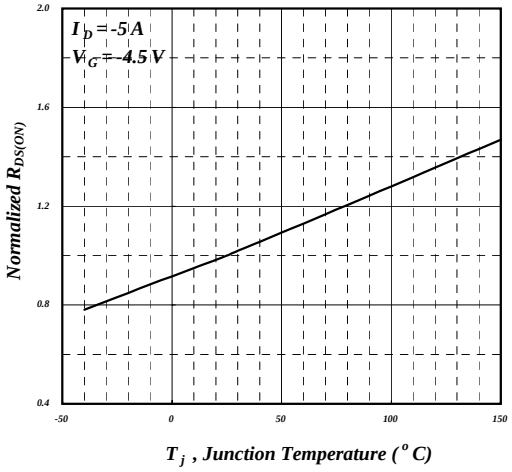


Fig 4. Normalized On-Resistance v.s. Junction Temperature

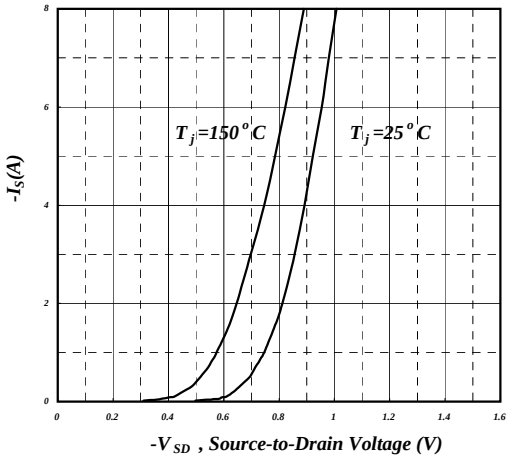


Fig 5. Forward Characteristic of Reverse Diode

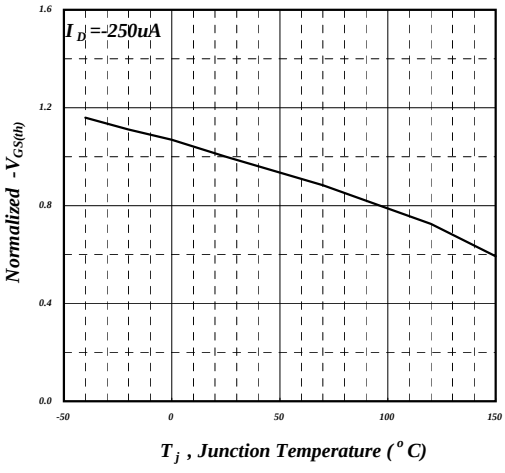


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

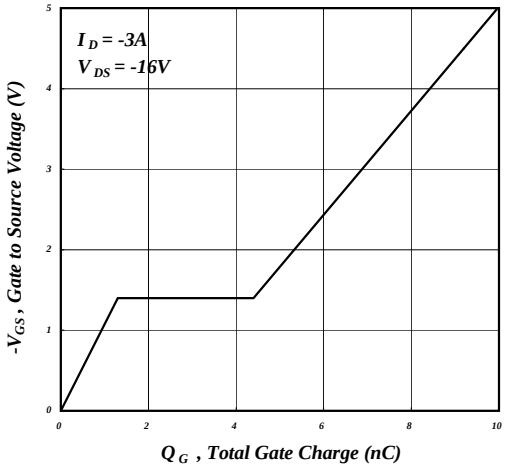


Fig 7. Gate Charge Characteristics

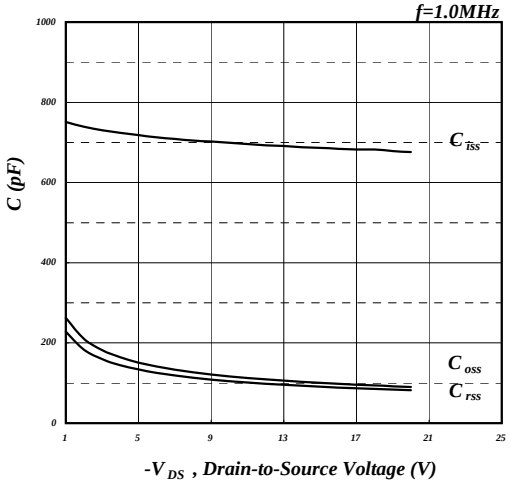


Fig 8. Typical Capacitance Characteristics

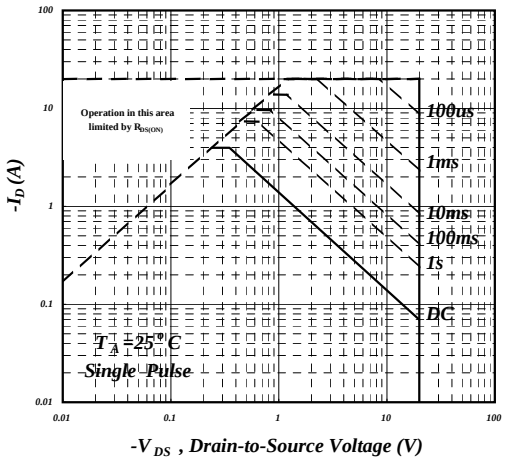


Fig 9. Maximum Safe Operating Area

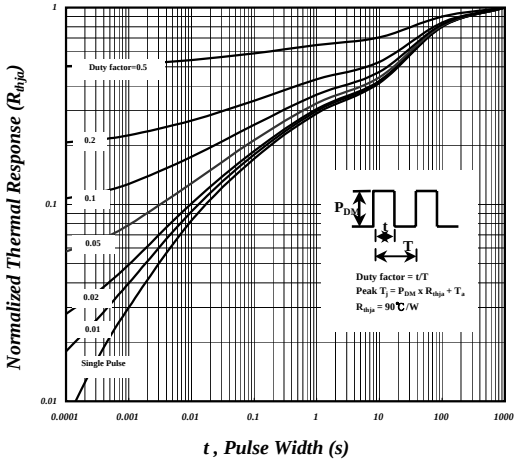


Fig 10. Effective Transient Thermal Impedance

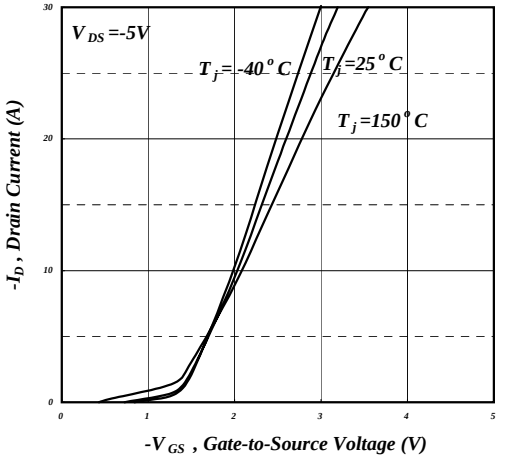


Fig 11. Transfer Characteristics

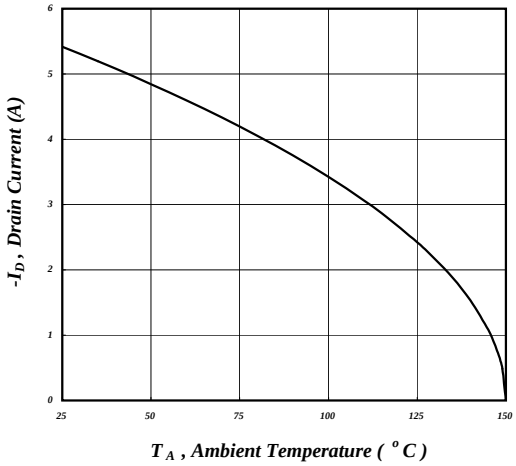


Fig 12. Maximum Continuous Drain Current v.s. Ambient Temperature